

# MA2J115

Silicon epitaxial planar type

For small power current rectification

## ■ Features

- Small S-mini type package, allowing high-density mounting
- High reverse voltage  $V_R$

## ■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

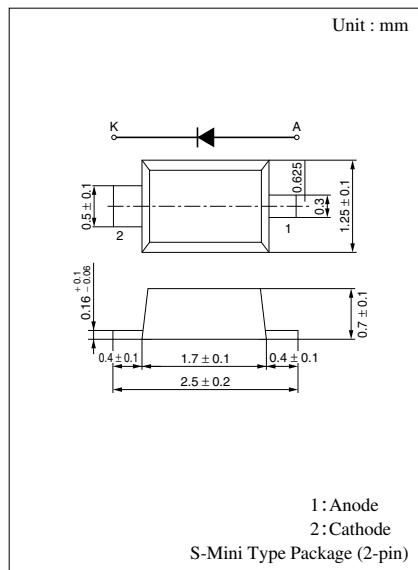
Parameter	Symbol	Rating	Unit
Reverse voltage (DC)	$V_R$	200	V
Peak reverse voltage	$V_{RM}$	200	V
Output current	$I_O$	200	mA
Repetitive peak forward current	$I_{FRM}$	600	mA
Non-repetitive peak forward surge current*	$I_{FSM}$	1	A
Junction temperature	$T_j$	150	$^\circ\text{C}$
Storage temperature	$T_{stg}$	-55 to +150	$^\circ\text{C}$

Note) \* :  $t = 1 \text{ s}$

## ■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Reverse current (DC)	$I_R$	$V_R = 200 \text{ V}$			200	nA
Forward voltage (DC)	$V_F$	$I_F = 200 \text{ mA}$			1.2	V
Terminal capacitance	$C_t$	$V_R = 0 \text{ V}, f = 1 \text{ MHz}$		4.5		pF

Note) Rated input/output frequency: 3 MHz



Marking Symbol: 1F

